

Appl. No. 10/605,678
Amdt. dated December 19, 2005
Reply to Office action of September 22, 2005

Listing of Claims:

Claim 1 (previously presented). A method of forming a gate structure comprising:

- 5 providing a substrate, and consecutively forming a gate oxide layer,
a polysilicon layer, a silicide layer, and a cap layer onto the substrate;
patterning the cap layer and the silicide layer to form a first
stacked gate structure;
removing a portion of the silicide layer exposed on sidewalls of
the first stacked gate structure for forming a recess on the sidewalls of
10 the first stacked gate structure;
filling a passivation layer into the recess to form a second stacked
gate structure; and
removing the polysilicon layer and the gate oxide layer using the
second stacked gate structure as a mask.

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Claims 2-3 (cancelled)

Claim 4 (previously presented) The method of claim 1 wherein forming the first stacked gate structure comprises:

- 20 forming a patterned silicon oxynitride layer; and
utilizing the patterned silicon oxynitride layer as a hard mask to
remove the cap layer, the silicide layer, and a portion of the polysilicon
layer not covered by the patterned silicon oxynitride layer.

- 25 Claim 5 (previously presented) The method of claim 4 further comprising a
step of removing the patterned polysilicon oxynitride layer after removing
the polysilicon layer and the gate oxide layer.

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Claim 6 (original) The method of claim 1 wherein the silicide layer comprises tungsten silicon.

Claim 7 (original) The method of claim 1 wherein the recess is formed by
5 removing a portion of the silicide layer using an ammonium hydrogen peroxide mixture (APM) solution.

Claim 8 (original) The method of claim 1 wherein the passivation layer comprises silicon nitride.

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Claim 9 (original) The method of claim 1 wherein filling the passivation layer into the recess further comprises:

depositing a silicon nitride layer onto the polysilicon layer and filling the recess; and

15 performing an anisotropic etching process to remove the silicon nitride layer outside the recess.

Claim 10 (previously presented) A method of forming a gate structure comprising:

20 providing a substrate, and consecutively forming a gate oxide layer, a polysilicon layer, a silicide layer, and a cap layer onto the substrate;

forming a patterned mask layer on the cap layer;

patterning the cap layer and the silicide layer to form a first stacked gate structure using the patterned mask layer as a mask;

25 removing a portion of the silicide layer exposed on sidewalls of the first stacked gate structure with an etching solution to form a recess;

depositing a passivation layer onto the polysilicon layer and filling

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the recess, and performing an anisotropic etching process to remove the passivation layer besides the passivation layer filed in the recess to form a second stacked gate structure;

5 removing the polysilicon layer and the gate oxide layer using the second stacked gate structure as a mask; and removing the patterned mask layer.

Claim 11 (original) The method of claim 10 wherein the patterned mask layer comprises silicon oxynitride.

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Claim 12 (original) The method of claim 10 wherein the steps of forming the patterned mask layer comprises:

forming a silicon oxynitride layer on the cap layer;
coating a photoresist layer on the silicon oxynitride;
15 performing an exposure process and a development process by using a photo mask to form a photoresist pattern;
utilizing the photoresist pattern as a hard mask to remove the silicon oxynitride not covered by the photoresist pattern; and removing the photoresist pattern.

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Claim 13 (original) The method of claim 10 wherein the silicide layer comprises tungsten silicon.

Claim 14 (original) The method of claim 10 wherein the etching solution is
25 an ammonium hydrogen peroxide mixture (APM) solution.

Claim 15 (original) The method of claim 10 wherein the passivation layer comprises silicon nitride.